# N-Channel 60-V (D-S) MOSFET

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

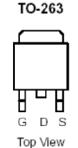
<b>Typical</b>	∣ App	lications:
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- · Automotive Systems
- DC/DC Conversion Circuits
- Battery Powered Power Tools

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
60	$4.2 @ V_{GS} = 10V$	90°a		
60	4.8 @ V <sub>GS</sub> = 4.5V	90"		







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			60	V		
Gate-Source Voltage			±20	V		
Continuous Drain Current a	T <sub>C</sub> =25°C	I <sub>D</sub>	90	Α		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	360	^		
Continuous Source Current (Diode Conduction) <sup>a</sup> T <sub>C</sub> =25°C		I <sub>S</sub>	90	Α		
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	$P_{D}$	300	W		
Operating Junction and Storage Temperature Range			-55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient °	$R_{\theta JA}$	62.5	°C/W			
Maximum Junction-to-Case	$R_{\theta JC}$	0.5	C/VV			

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#### Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

### **Electrical Characteristics**

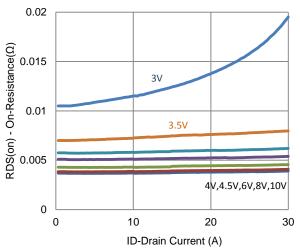
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current		$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA			
Zero Gate Voltage Brain Gurrent	I <sub>DSS</sub>	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	C 10			u/\		
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α		
Drain-Source On-Resistance <sup>a</sup>	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			4.2	mΩ		
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$			4.8	11122		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		21		S		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 45 \text{ A}, V_{GS} = 0 \text{ V}$		0.94		V		
		Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$	$V_{DS} = 30 \text{ V}, V_{GS} = 4.5 \text{ V},$		57		nC		
Gate-Source Charge	$Q_gs$	$I_{D} = 20 \text{ A}$		19				
Gate-Drain Charge	$Q_gd$	1 <sub>D</sub> = 23 / X		20				
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 30 \text{ V}, R_1 = 1.5 \Omega,$		20				
Rise Time	t <sub>r</sub>	$I_{DS} = 30 \text{ V}, N_{L} = 1.3 \Omega_{2},$ $I_{D} = 20 \text{ A},$		18		ns		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		161				
Fall Time	t <sub>f</sub>	VGEN = 10 V; NGEN 0 12		39				
Input Capacitance	C <sub>iss</sub>			10350		_		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		396		pF		
Reverse Transfer Capacitance	$C_{rss}$			330				

#### Notes

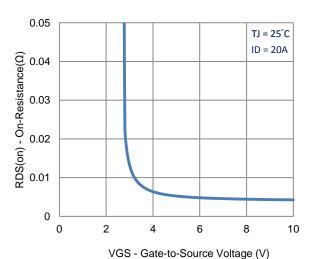
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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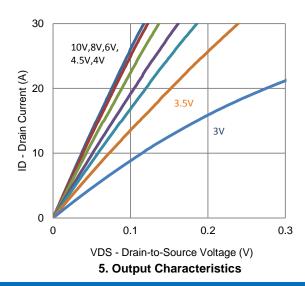
## **Typical Electrical Characteristics**

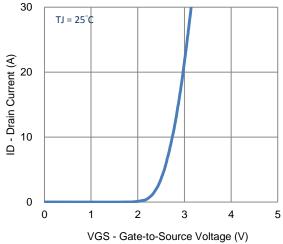


#### 1. On-Resistance vs. Drain Current

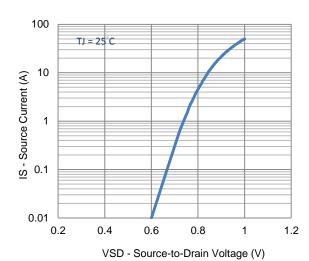


3. On-Resistance vs. Gate-to-Source Voltage

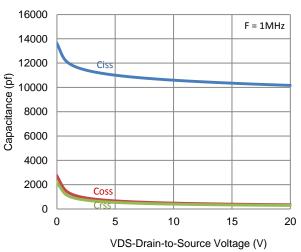




2. Transfer Characteristics

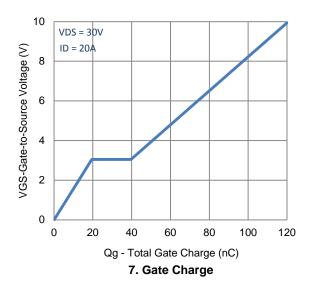


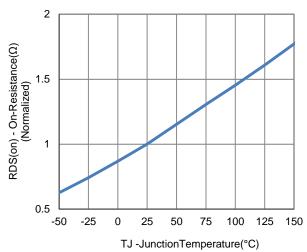
4. Drain-to-Source Forward Voltage



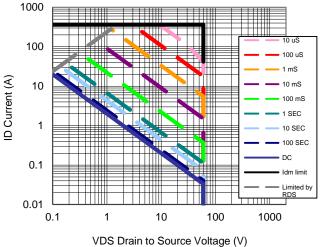
6. Capacitance

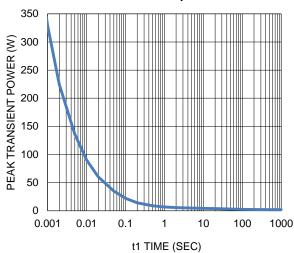
## **Typical Electrical Characteristics**





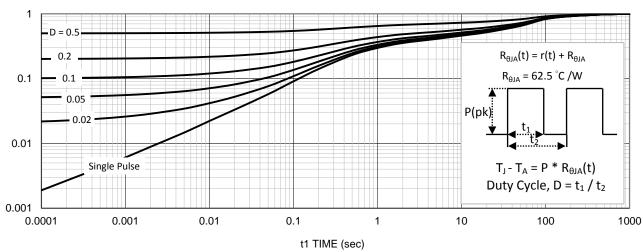
8. Normalized On-Resistance Vs Junction Temperature





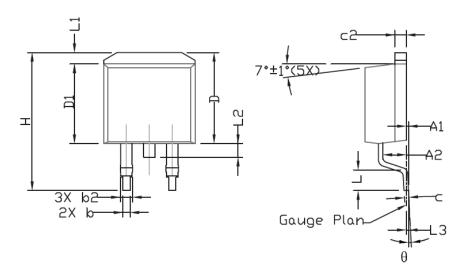
9. Safe Operating Area

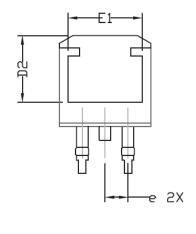
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

# **Package Information**





CVAREI	<u>DIMENZITINAL KEMMIZI INCHEZ KEMMIZ</u>					SIMI2
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX
Α	4,30	4.57	4,72	0.169	0.180	0.186
A1	0		0.25	0		0.010
A2	2,47	2.57	2,67	0.097	0.101	0.105
b	0.69	0,813	0.94	0.027	0.032	0.037
b2	1.17	1.27	1,45	0.046	0.050	0.057
C	0.48	0,50	0,60	0.019	0.020	0.024
c2	1,17	1.27	1.37	0,046	0,050	0,054
D	9,80	10.05	10.30	0.386	0,396	0.406
D1	8,64	8.78	9,65	0,340	0,346	0,380
D2	7.12	7.37	7,62	0.280	0.290	0,300
E	9,70	10.15	10.54	0,382	0.400	0.415
E1	8,00	8,20	8,40	0.315	0,323	0.331
е	2.	54 BSC		0.	100 BSC	_
Н	14,99	15,24	15,49	0.590	0.600	0.610
L	1,78	2.29	2.79	0.070	0.090	0.110
L1	1,02	1.27	1.52	0.040	0.050	0,060
L2			1.75			0.069
L3		0,254			0.010	
θ	0.		8*	0*		8.